**Product data sheet** 

## 1. General description

Silicon Carbide Schottky diode in a TO220-2L plastic package, designed for high frequency switched-mode power supplies.





### 2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I<sub>FSM</sub>
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- · Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- · Motor Drives

### 4. Quick reference data

### Table 1. Quick reference data

| Symbol             | Parameter                       | Conditions  |     | Va  | lues |     | Unit |
|--------------------|---------------------------------|---|-----|-----|------|-----|------|
| Absolute           | maximum rating                  |   |     |     |      |     |      |
| $V_{RRM}$          | repetitive peak reverse voltage |   |     | 6   | 50   |     | V    |
| I <sub>F(AV)</sub> | average forward current         | $\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 124 °C;<br>Fig. 1; Fig. 2; Fig. 3                         | 6   |     | А    |     |      |
| T <sub>j</sub>     | junction temperature            |   | 175 |     | °C   |     |      |
| Symbol             | Parameter                       | Conditions  |     | Min | Тур  | Max | Unit |
| Static ch          | aracteristics                   |   |     |     |      |     |      |
| V <sub>F</sub>     | forward voltage                 | I <sub>F</sub> = 6 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>   |     | -   | 1.5  | 1.7 | V    |
|                    |                                 | I <sub>F</sub> = 6 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>  |     | -   | 1.8  | 2.1 | V    |
| Dynamic            | characteristics                 |   |     |     | ,    |     |      |
| Q <sub>r</sub>     | recovered charge                | $I_F = 6 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s}; V_R = 400 \text{ V};$<br>$T_j = 25 \text{ °C}; Fig. 7$ |     | -   | 9    | -   | nC   |
|                    |                                 |   |     |     |      |     |      |

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description                         | Simplified outline | Graphic symbol     |
|-----|--------|-------------------------------------|--------------------|--------------------|
| 1   | K      | cathode                             | mb                 | v 14 A             |
| 2   | А      | anode                               | 1 7 5              | K — A<br>001aaa020 |
| mb  | mb     | mounting base; connected to cathode |                    |                    |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number |          | Orderable part number |        | Small packing | Package | Package     |
|-------------|----------|-----------------------|--------|---------------|---------|-------------|
|             | name     |                       | method | quantity      | version | issue date  |
| NXPSC06650  | TO220-2L | NXPSC066506Q          | Tube   | 50            | SOD59A  | 30-Mar-2015 |

# 7. Marking

### Table 4. Marking codes

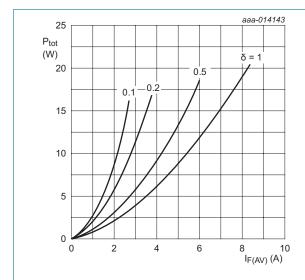
| Marking codes  |
|----------------|
| NXPSC<br>06650 |
|                |

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                       | Conditions   | Values     | Unit             |
|--------------------|---------------------------------|--|------------|------------------|
| $V_{RRM}$          | repetitive peak reverse voltage |  | 650        | V                |
| $V_{RWM}$          | crest working reverse voltage   |  | 650        | V                |
| $V_R$              | reverse voltage                 | DC   | 650        | V                |
| I <sub>F(AV)</sub> | average forward current         | $δ$ = 0.5; square-wave pulse; $T_{mb} \le 124$ °C;<br>Fig. 1; Fig. 2; Fig. 3           | 6          | А                |
| I <sub>FRM</sub>   | repetitive peak forward current | $\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 124 °C;<br>square-wave pulse | 12         | А                |
| I <sub>FSM</sub>   | non-repetitive peak             | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                                  | 36         | Α                |
|                    | forward current                 | $t_p$ = 10 μs; $T_{j(init)}$ = 25 °C; square-wave pulse                                | 310        | А                |
| l <sup>2</sup> t   | I <sup>2</sup> t for fusing     | sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$                 | 6.48       | A <sup>2</sup> s |
| T <sub>stg</sub>   | storage temperature             |  | -55 to 175 | °C               |
| T <sub>j</sub>     | junction temperature            |  | 175        | °C               |



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$  $V_o = 0.444 \text{ V}; R_s = 0.2192 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

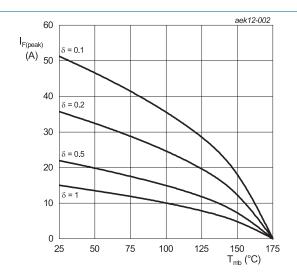


Fig. 2. Current derating as a function of mounting base temperature

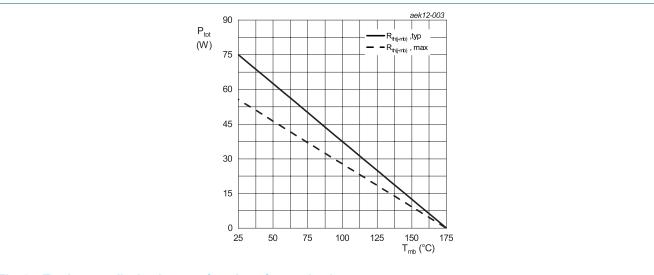
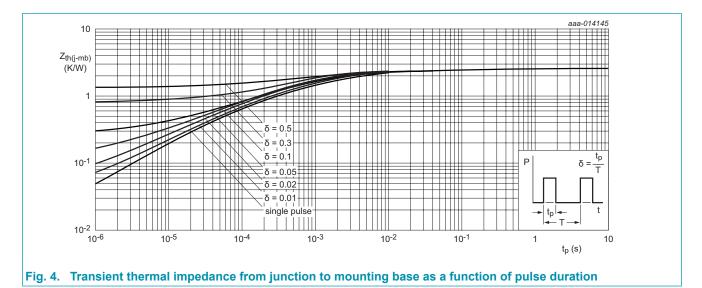


Fig. 3. Total power dissipation as a function of mounting base temperature

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

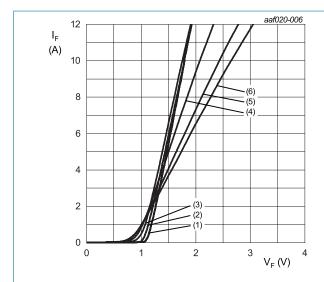
| Symbol                | Parameter  | Conditions                     | Min | Тур | Max | Unit |
|-----------------------|--|--------------------------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base    | with heatsink compound; Fig. 4 | -   | 2   | 2.7 | K/W  |
| $R_{\text{th(j-a)}}$  | thermal resistance<br>from junction to<br>ambient free air | in free air                    | -   | 60  | -   | K/W  |



## 10. Characteristics

**Table 7. Characteristics** 

| Symbol          | Parameter         | Conditions  |   | Min | Тур | Max | Unit |
|-----------------|-------------------|---|---|-----|-----|-----|------|
| Static cha      | racteristics      |   |   |     |     |     |      |
| V <sub>F</sub>  | forward current   | I <sub>F</sub> = 6 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>   |   | -   | 1.5 | 1.7 | V    |
|                 |                   | I <sub>F</sub> = 6 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>  |   | -   | 1.8 | 2.1 | V    |
| I <sub>R</sub>  | reverse current   | V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   |   | -   | -   | 40  | μA   |
|                 |                   | V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  |   | -   | -   | 160 | μA   |
| Dynamic         | characteristics   |   | , |     |     |     | _    |
| Q <sub>r</sub>  | recovered charge  | $I_F = 6 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$ |   | -   | 9   | -   | nC   |
| C <sub>d</sub>  | diode capacitance | f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C   |   | -   | 190 | -   | pF   |
|                 |                   | f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C   |   | -   | 30  | -   | pF   |
|                 |                   | f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C   |   | -   | 29  | -   | pF   |
| E <sub>as</sub> | non-repetitive    | $I_R = 4.25 \text{ A}; L = 5 \text{ mH}; T_{j(init)} = 25 \text{ °C}$   |   | 45  | -   | -   | mJ   |
|                 | avalanche energy  |   |   |     |     |     |      |



 $V_o = 0.444 \text{ V}; R_s = 0.2192 \Omega$ 

(1)  $T_i = -55$  °C; typical values

(2) T<sub>i</sub> = 0 °C; typical values

(3) T<sub>j</sub> = 25 °C; typical values (4) T<sub>j</sub> = 100 °C; typical values

(5) T<sub>i</sub> = 150 °C; typical values (6) T<sub>i</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward

voltage; typical values

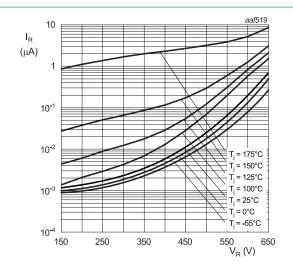


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

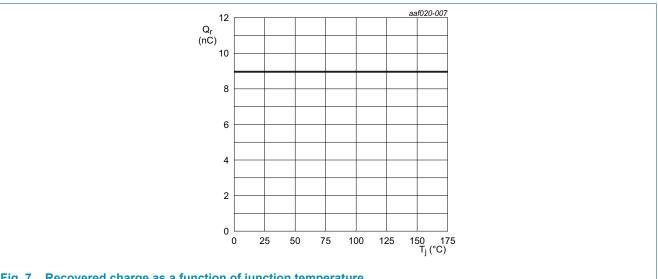
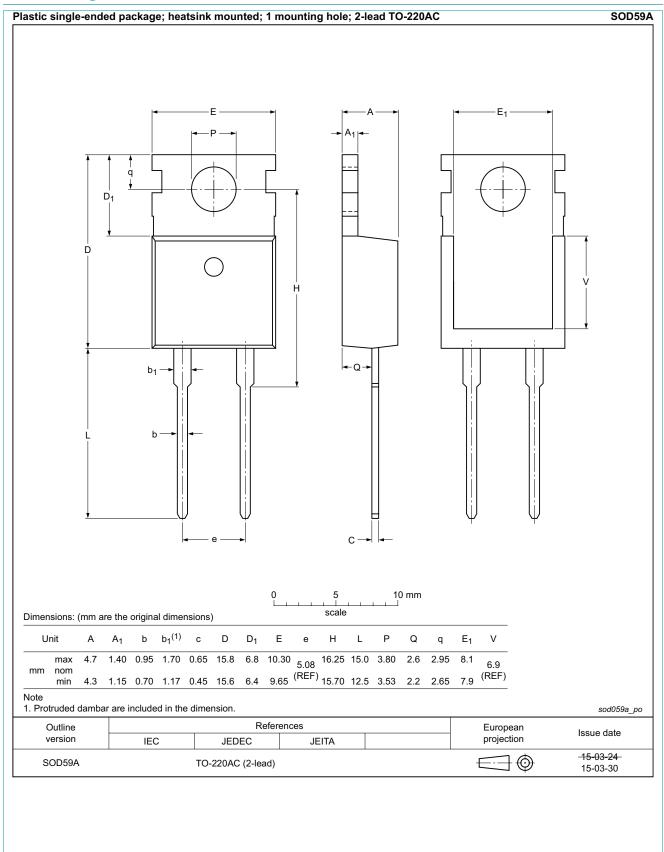


Fig. 7. Recovered charge as a function of junction temperature

# 11. Package outline



## 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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Date of release: 06 November 2019

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